

Characteristic			Symbol	Value	Units
Drain-Source Voltage			V_{DSS}	25	V
Gate-Source Voltage			V_{GSS}	8	V
Continuous Drain Current (Note 6) V _{GS} = 4.5V	Steady State	$T_A = +25$ °C $T_A = +70$ °C	I _D	0.26 0.21	А
Continuous Drain Current (Note 6) V _{GS} = 2.7V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I _D	0.23 0.18	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I _{DM}	1.5	Α
Maximum Body Diode Continuous Current (Note 6)			Is	0.5	А

Thermal Characteristics

Characteristic		Symbol	Value	Units
Total Dawar Dissination	(Note 5)	Ь	0.32	W
Total Power Dissipation	(Note 6)	P _D	0.4	
Thermal Resistance, Junction to Ambient	(Note 5)	В	369	°C/W
	(Note 6)	$R_{\theta JA}$	296	
Thermal Resistance, Junction to Case	(Note 6)	R ₀ JC	115	
Operating and Storage Temperature Range		T _{J,} T _{STG}	-55 to +150	°C

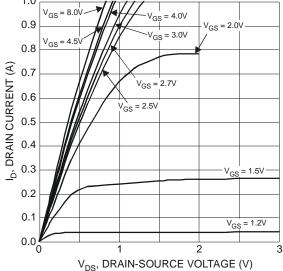
Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)							
Drain-Source Breakdown Voltage	BV _{DSS}	25	_	_	V	V _{GS} = 0V, I _D = 250μA	
Zero Gate Voltage Drain Current	I _{DSS}	_	_	1.0	μA	V _{DS} = 20V, V _{GS} = 0V	
Gate-Body Leakage	I _{GSS}		_	100	nA	$V_{GS} = 8V$, $V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)							
Gate Threshold Voltage	V _{GS(th)}	0.7	_	1.1	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance	D		_	4	Ω	$V_{GS} = 4.5V, I_D = 0.4A$	
Static Diani-Source Off-Resistance	R _{DS(ON)}		_	5	Ω	$V_{GS} = 2.7V, I_D = 0.2A$	
Forward Transconductance	g _{FS}	_	1	_	S	$V_{DS} = 5V, I_D = 0.4A$	
Diode Forward Voltage	V _{SD}	_	0.76	1.2	V	V _{GS} = 0V, I _S = 0.29A	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	_	27.9	42	pF	$V_{DS} = 10V, V_{GS} = 0V,$ f = 1.0MHz	
Output Capacitance	Coss	_	6.1	9.2			
Reverse Transfer Capacitance	Crss	_	2.0	3.0			
Gate Resistance	Rg	_	26.4	_	Ω	$V_{DS} = 0V$, $V_{GS} = 0V$, $f = 1MHz$	
Total Gate Charge	Qg	_	0.36	_			
Gate-Source Charge	Qgs	_	0.06	_	nC	$V_{GS} = 4.5V, V_{DS} = 5V,$ $I_{D} = 0.2A$	
Gate-Drain Charge	Q_{gd}	_	0.04	_			
Turn-On Delay Time	t _{D(on)}	_	2.9	_		V _{GS} = 4.5V, V _{DS} = 6V	
Turn-On Rise Time	t _r	_	1.8	_	nS		
Turn-Off Delay Time	t _{D(off)}	_	6.6	_	nS	$I_D = 0.5A, R_G = 50\Omega$	
Turn-Off Fall Time	t _f	_	2.3	_			

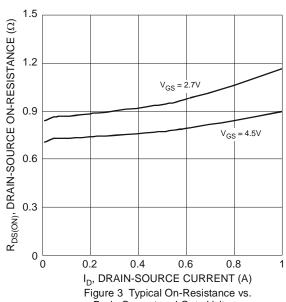
5. Device mounted on FR-4 PC board, with minimum recommended pad layout, single sided. Notes:

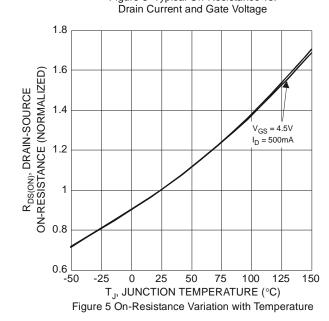
Device mounted on FR-4 Fc board, with minimum recommended pad rayout, single sided.
 Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper pad layout 7. Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

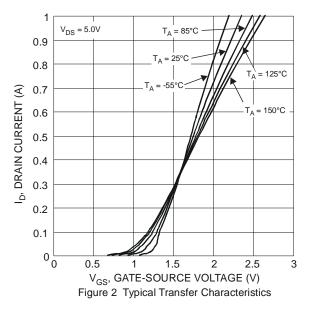


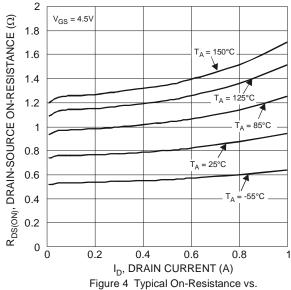


V_{DS}, DRAIN-SOURCE VOLTAGE (V)
Figure 1 Typical Output Characteristics









Drain Current and Temperature

1.5 $R_{DS(OM)}$, DRAIN-SOURCE ON-RESISTANCE (Ω) 1.2 V_{GS} = 4.5V I_D = 500mA 0.9 0.3 -50 -25 25 50 75 100 125 150 T_J , JUNCTION TEMPERATURE (°C)

Figure 6 On-Resistance Variation with Temperature



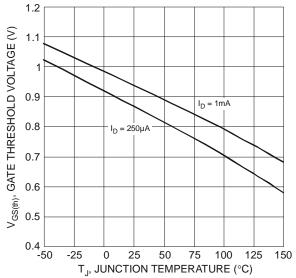
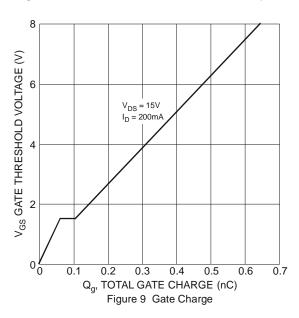
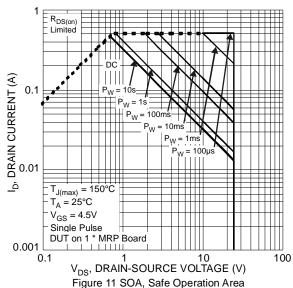
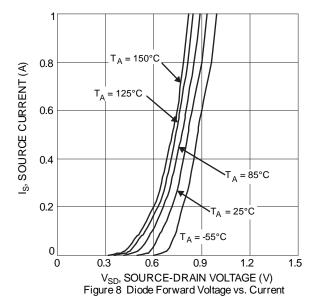
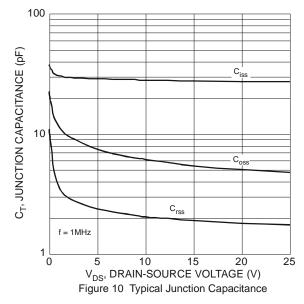


Figure 7 Gate Threshold Variation vs. Ambient Temperature

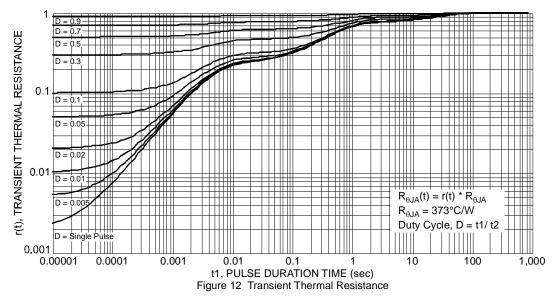






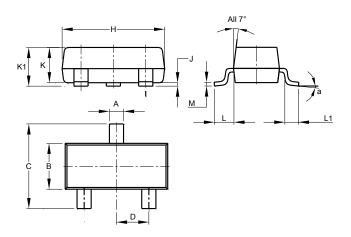






Package Outline Dimensions

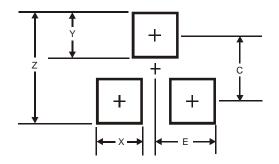
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for latest version.



SOT23						
Dim	Min	Max	Тур			
Α	0.37	0.51	0.40			
В	1.20	1.40	1.30			
С	2.30	2.50	2.40			
D	0.89	1.03	0.915			
F	0.45	0.60	0.535			
G	1.78	2.05	1.83			
Н	2.80	3.00	2.90			
7	0.013	0.10	0.05			
K	0.890	1.00	0.975			
K1	0.903	1.10	1.025			
٦	0.45	0.61	0.55			
L1	0.25	0.55	0.40			
М	0.085	0.150	0.110			
а	8°					
All Dimensions in mm						

Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)		
Z	2.9		
Х	0.8		
Y	0.9		
С	2.0		
E	1.35		



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